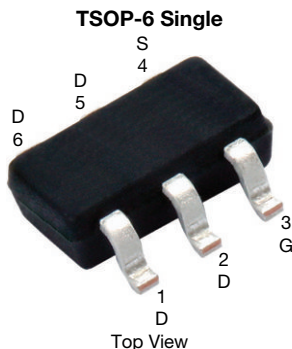


Automotive N-Channel 60 V (D-S) 175 °C MOSFET



Marking Code: 9Hxxx

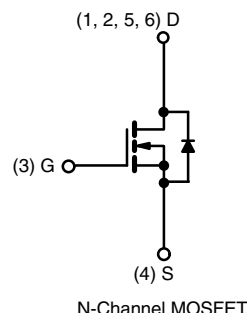
PRODUCT SUMMARY	
V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.042
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.063
I_D (A)	7
Configuration	Single

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE



ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and halogen-free	SQ3426CEV (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	60	V
Gate-source voltage		V _{GS}	± 20	
Continuous drain current	T _C = 25 °C	I _D	7	A
	T _C = 125 °C		4	
Continuous source current (diode conduction)		I _S	6	
Pulsed drain current ^a		I _{DM}	29	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	10	
Single pulse avalanche energy		E _{AS}	5	mJ
Maximum power dissipation	T _C = 25 °C	P _D	5	W
	T _C = 125 °C		1.6	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction to ambient	PCB mount ^b	R_{thJA}	110	°C/W
Junction to foot (drain)		R_{thJF}	30	

Notes

- a. Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
b. When mounted on 1" square PCB (FR4 material)



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		60	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.5	2	2.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V		-	-	± 100	nA
		V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 300	
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	10	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 5 A	-	0.034	0.042	Ω
		V _{GS} = 10 V	I _D = 5 A, T _J = 125 °C	-	-	0.073	
		V _{GS} = 10 V	I _D = 5 A, T _J = 175 °C	-	-	0.092	
		V _{GS} = 4.5 V	I _D = 4 A	-	0.037	0.063	
Forward transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 4 A		-	21	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 30 V, f = 1 MHz	-	718	790	pF
Output Capacitance	C _{oss}			-	75	110	
Reverse Transfer Capacitance	C _{rss}			-	29	70	
Total Gate Charge ^c	Q _g	V _{GS} = 4.5 V	V _{DS} = 30 V, I _D = 4 A	-	6.8	12	nC
Gate-Source Charge ^c	Q _{gs}			-	2.9	-	
Gate-Drain Charge ^c	Q _{gd}			-	2.0	-	
Gate Resistance	R _g	f = 1 MHz		1.9	3.1	5.7	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 7.5 Ω I _D ≅ 4 A, V _{GEN} = 10 V, R _g = 1 Ω		-	9	14	ns
Rise Time ^c	t _r			-	3	18	
Turn-Off Delay Time ^c	t _{d(off)}			-	19	29	
Fall Time ^c	t _f			-	4	11	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	29	A
Forward voltage	V _{SD}	I _F = 1.6 A, V _{GS} = 0 V		-	0.77	1.2	V
Body diode reverse recovery time	t _{rr}	I _F = 4 A, di/dt = 100 A/μs		-	19	38	ns
Body diode reverse recovery charge	Q _{rr}			-	18	36	nC
Reverse recovery fall time	t _a			-	15	-	ns
Reverse recovery rise time	t _b			-	4	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-2.1	-	A

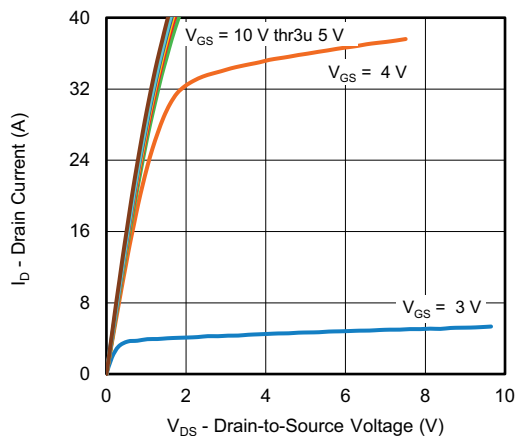
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

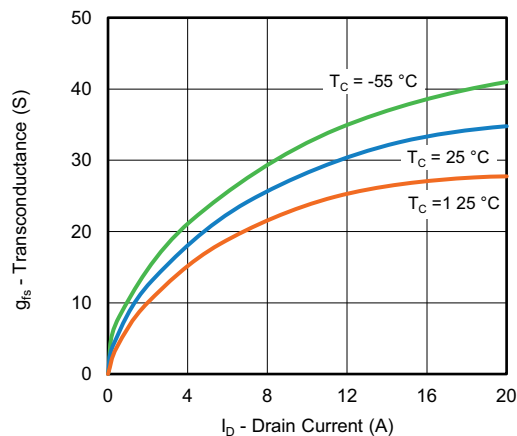
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



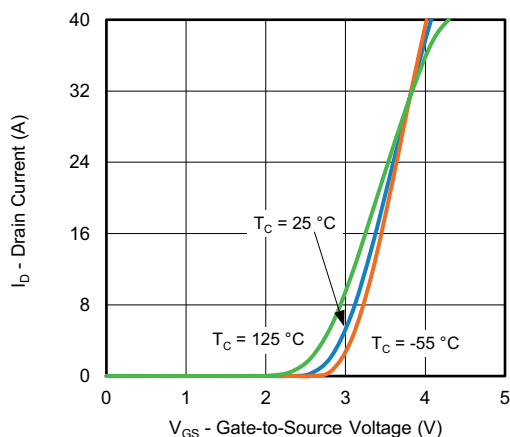
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



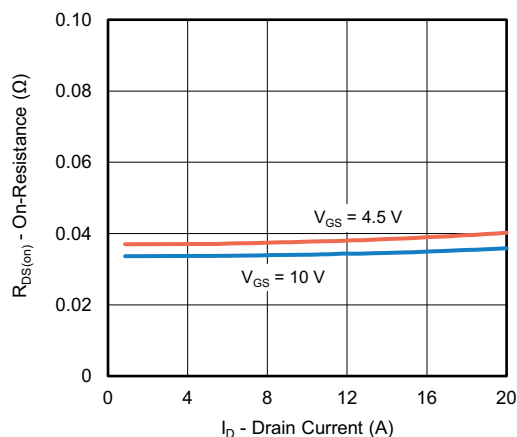
Output Characteristics



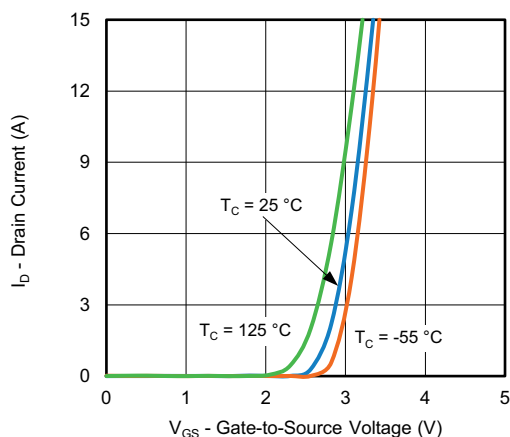
Transconductance



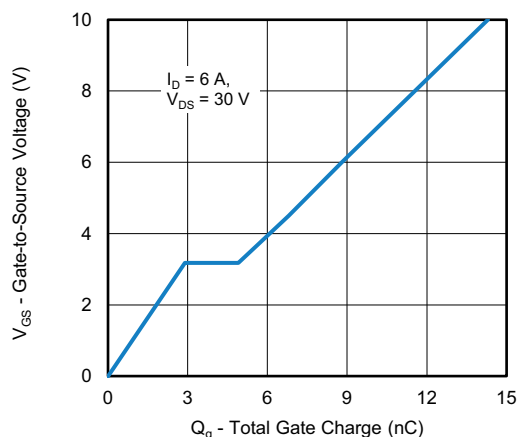
Transfer Characteristics



On-Resistance vs. Drain Current



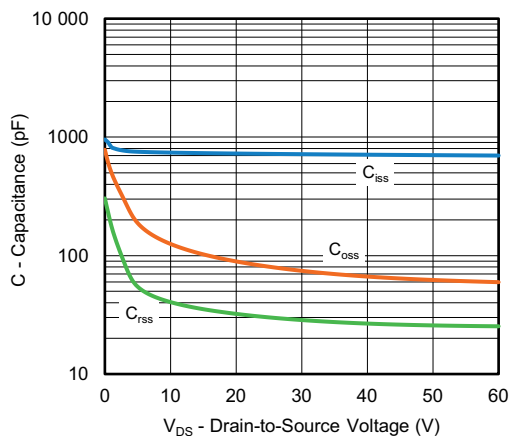
Transfer Characteristics



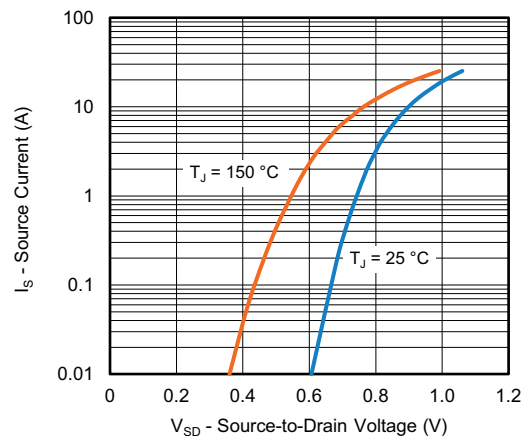
Gate Charge



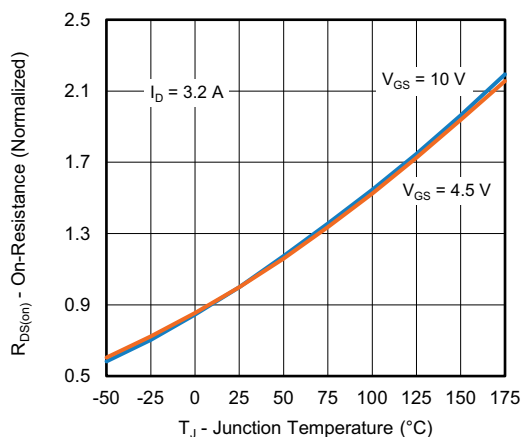
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



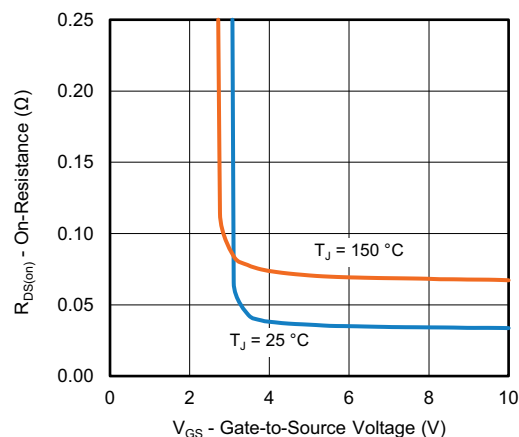
Capacitance



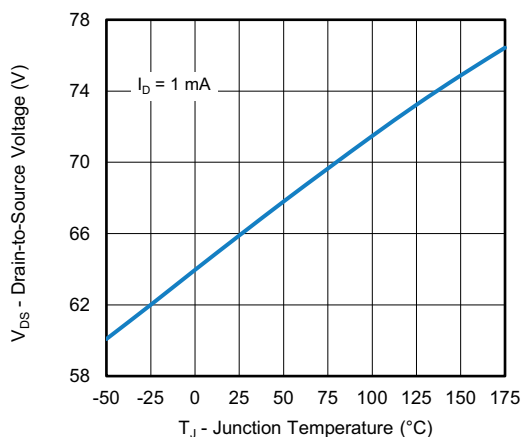
Source Drain Diode Forward Voltage



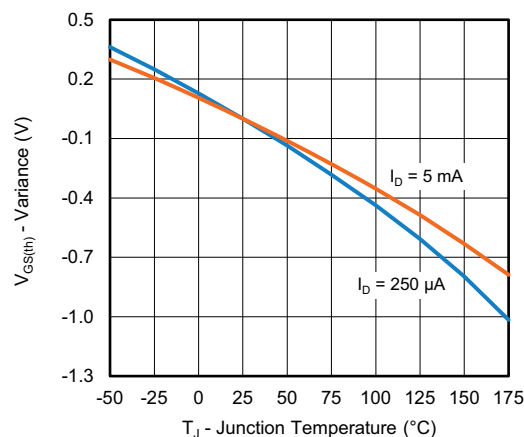
On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-Source Voltage



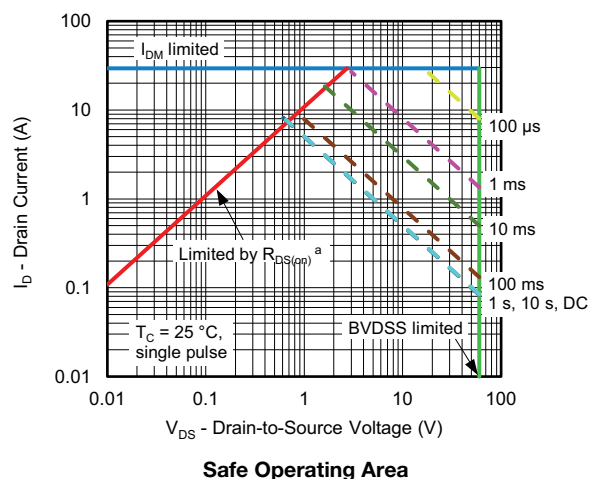
Drain Source Breakdown vs. Junction Temperature



Threshold Voltage

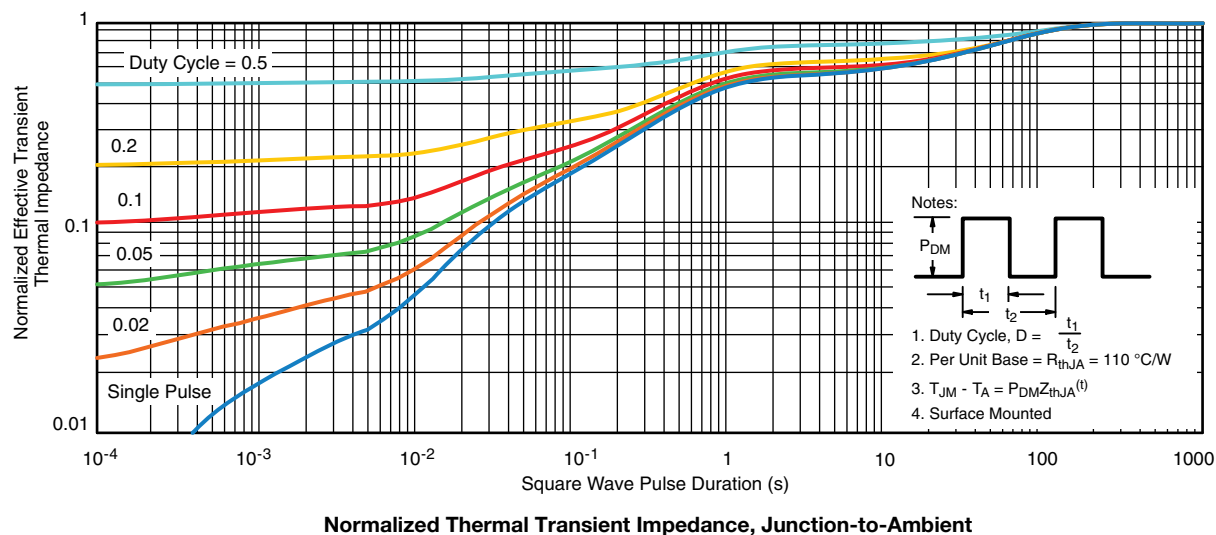


THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



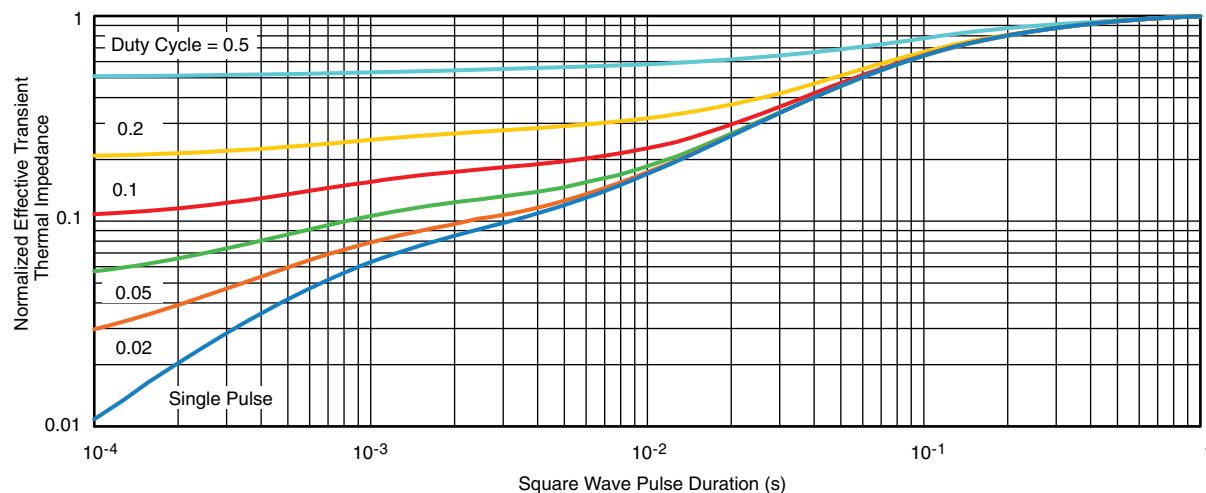
Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified





THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Normalized thermal Transient Impedance, Junction-to-Foot

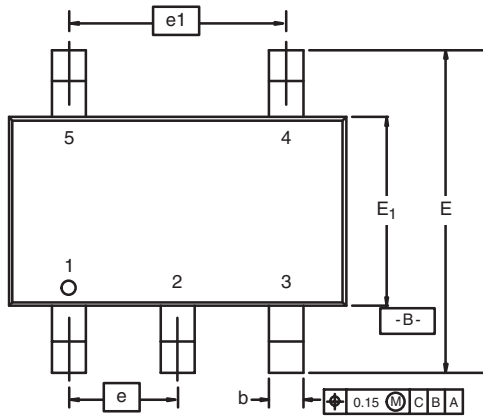
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

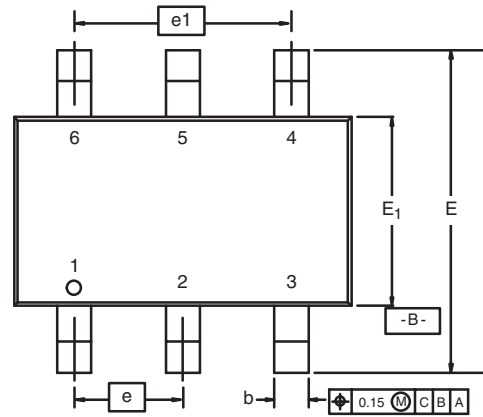
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TSOP: 5/6-LEAD

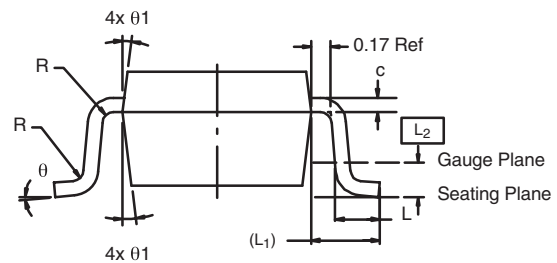
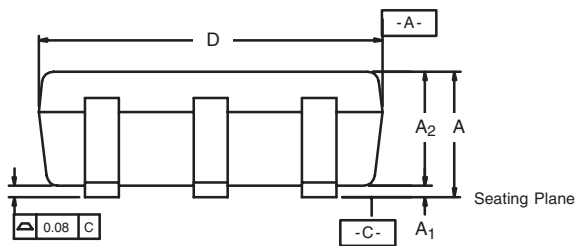
JEDEC Part Number: MO-193C



5-LEAD TSOP

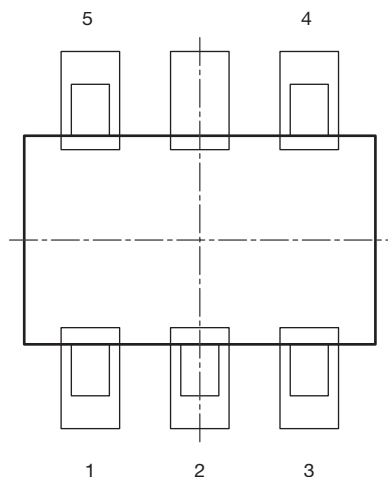


6-LEAD TSOP

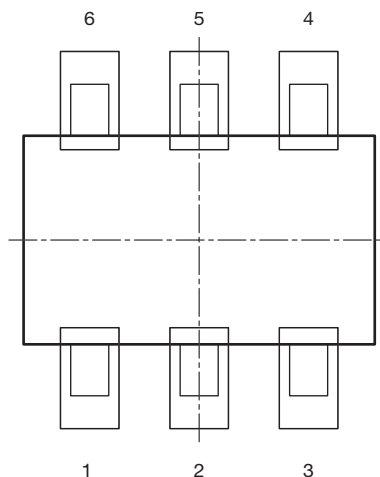


Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e ₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L ₁	0.60 Ref			0.024 Ref		
L ₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ ₁	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06						
DWG: 5540						

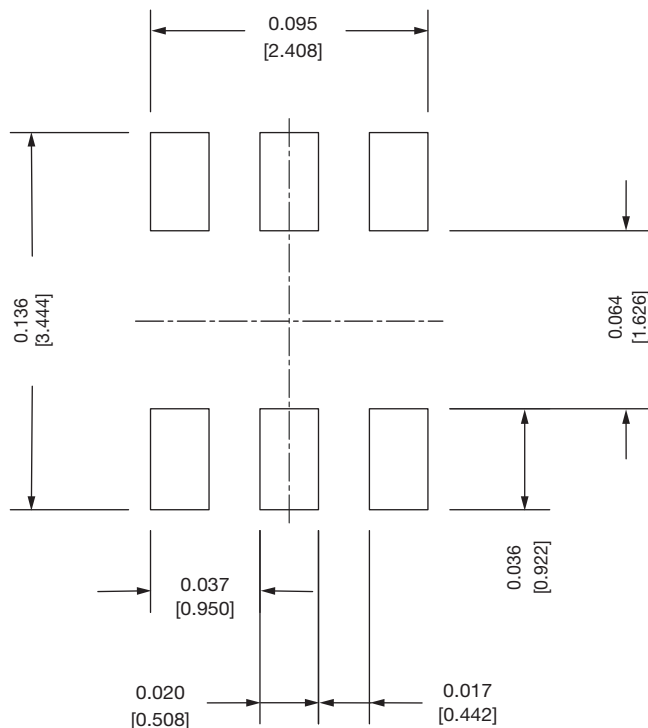
Recommended Land Pattern For TSOP-5L / TSOP-6L



TSOP 5L



TSOP 6L


Note

- All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022
DWG: 3010



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